

## Effective factors for current sharing:

	static	dynamic
commutation inductance	-	$\Delta L_{\sigma}$
driver	-	$\Delta L_{\text{wire}}, \Delta t_{\text{on}}, \Delta t_{\text{off}}$
device characteristics	$\Delta V_{\text{ce sat}}, \Delta T_j$	$\Delta T_j, \Delta t_{\text{d on}}, \Delta t_{\text{d off}}$

## Recommendations:

symmetrical design of IGBT current paths (identical stray inductances)

symmetrical design of gate driver (same driver stage, separate gate resistors, splitted  $R_g$  with appr. 1/3 of it in the emitter leads)

use devices of one production lot (smallest parameter deviations guaranteed)

symmetrical cooling conditions (identical heat-sink temperature and flow rate below the paralleled devices)

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## Gate driver:

